

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China









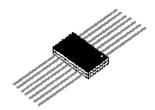
1N6100

Isolated Diode Array with HiRel MQ, MX, MV, and MSP Screening Options

DESCRIPTION

These low capacitance diode arrays are multiple, discrete, isolated junctions fabricated by a planar process and mounted in a 14-PIN package for use as steering diodes protecting up to seven I/O ports from ESD, EFT, or surge by directing them either to the positive side of the power supply line or to ground (see figure 1). An external TVS diode may be added between the positive supply line and ground to prevent overvoltage on the supply rail. They may also be used in fast switching coredriver applications. This includes computers and peripheral equipment such as magnetic cores, thin-film memories, plated-wire memories, etc., as well as decoding or encoding applications. These arrays offer many advantages of integrated circuits such as high-density packaging and improved reliability. This is a result of fewer pick and place operations, smaller footprint, smaller weight, and elimination of various discrete packages that may not be as user friendly in PC board mounting.

APPEARANCE



14-PIN Ceramic Flat Pack

IMPORTANT: For the most current data, consult MICROSEMI's website: http://www.microsemi.com

FEATURES

- Hermetic Ceramic Package
- Isolated Diodes to Eliminate Cross-Talk Voltages
- High Breakdown Voltage $V_{BR} > 75 \text{ V}$ at 5 μA
- Low Leakage I_R< 100 nA at 40 V
- Low Capacitance C < 4.0 pF
- Switching Speeds less than 10 ns
- Options for screening in accordance with MIL-PRF-19500/474 for JAN, JANTX, JANTXV, and JANS are available by adding MQ, MX, MV, or MSP prefixes respectively to part numbers. For example, designate MX1N6100 for a JANTX screen.

MAXIMUM RATINGS

- Reverse Breakdown Voltage of 75 Vdc (Note 1 & 2)
- Continuous Forward Current of 300 mA dc (Note 1 & 3)
- Peak Surge Current (tp=1/120 s) of 500 mA dc (Note 1)
- 400 mW Power Dissipation per Junction @ 25°C
- 500 mW Power Dissipation per Package @ 25°C (Note 4)
- Operating Junction Temperature range –65 to +150°C
- Storage Temperature range of –65 to +200°C

NOTE 1: Each Diode

NOTE 2: Pulsed: $P_W = 100$ ms max; duty cycle $\leq 20\%$ **NOTE 3:** Derate at 2.4 mA/°C above +25°C

NOTE 4: Derate at 4.0 mW/°C above +25°C

APPLICATIONS / BENEFITS

- High Frequency Data Lines
- RS-232 & RS-422 Interface Networks
- Ethernet: 10 Base T
- Computer I/O Ports
- LAN
- Switching Core Drivers
- IEC 61000-4 Compatible (See Circuit in Figure 1)

61000-4-2 (ESD): Air 15 kV, contact – 8 kV

61000-4-4 (EFT): 40 A - 5/50 ns 61000-4-5 (surge): 12 A, 8/20 µs

MECHANICAL AND PACKAGING

- 14-PIN Ceramic Flat Pack
- Weight 0.29 grams (approximate)
- Marking: Logo, part number, date code and dot identifying pin #1
- Carrier Tubes; 19 pcs (standard)

ELECTRICAL CHARACTERISTICS (Per Diode) @25°C unless otherwise specified										
	MAXIMUM FORWARD VOLTAGE V _{F1} I _F = 100 mA	MAXIMUM REVERSE CURRENT	MAXIMUM REVERSE CURRENT	MAXIMUM CAPACITANCE (PIN TO PIN) Ct VR = 0 V	MAXIMUM FORWARD RECOVERY TIME t _{fr}	MAXIMUM REVERSE RECOVERY TIME trr $I_F = I_R = 10 \text{ mAdc}$ $i_{rr} = 1 \text{ mAdc}$	MAXIMUM FORWARD VOLTAGE MATCH V _{F5}			
PART	(Note 1)	$V_R = 40 \text{ V}$	V _R = 20 V	F = 1 MHz	I _F = 100 mA	R _L = 100 ohms	I _F = 10 mA			
NUMBER	V	μΑ	nA	pF	ns	ns	mV			
1N6100	1	0.1	25	4.0	15	10	5			

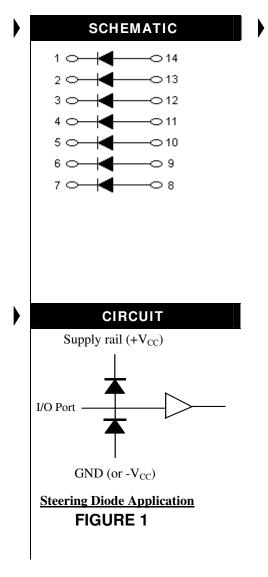
NOTE 1: Pulsed: $P_W = 300 \,\mu s + -50 \,\mu s$, duty cycle $\leq 2\%$, 90 μs after leading edge.



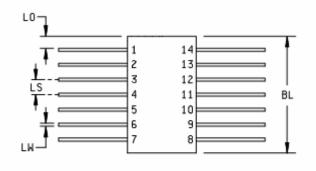
1N6100

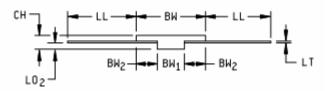
Isolated Diode Array with HiRel MQ, MX, MV, and MSP Screening Options

	SYMBOLS & DEFINITIONS
Symbol	DEFINITION
V_{BR}	Minimum Breakdown Voltage: The minimum voltage the device will exhibit at a specified current.
V_{F}	Maximum Forward Voltage: The maximum forward voltage the device will exhibit at a specified current.
I _R	Maximum Leakage Current: The maximum leakage current that will flow at the specified voltage and temperature.
C _t	Capacitance: The capacitance of the TVS as defined @ 0 volts at a frequency of 1 MHz and stated in picofarads.



PACKAGE DIMENSIONS





Symbol	Inches		Millimeters	
	Min	Max	Min	Max
BL		.390		9.91
BW	.235	.260	5.97	6.60
CH	.045	.095	1.14	2.41
LL	.250	.370	6.35	9.40
LO	.005		0.13	
LO ₂	.026	.045	0.66	1.14
LS	.050 BSC		1.27 BSC	
LT	.003	.006	0.08	0.15
LU		.280		7.11
LW	.010	.019	0.25	0.48